



# 30V N 通道 NexFET™ 功率金属氧化物场效应晶体管 (MOSFET)

查询样品: CSD17551Q5A

## 特性

- 超低栅极电荷 (Qg) 和栅漏电荷 (Qgd)
- 低热阻
- 额定雪崩能量
- 无铅端子封装
- 符合 RoHS 标准
- 无卤素
- 小外形尺寸 (SON) 5mm x 6mm 塑料封装

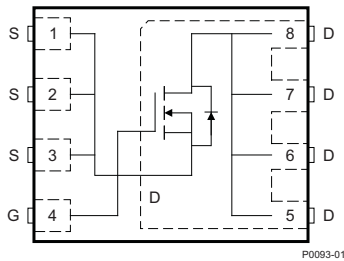
## 应用范围

- 网络互联、电信和计算系统中的负载点同步降压
- 为控制场效应晶体管 (FET) 应用进行了优化

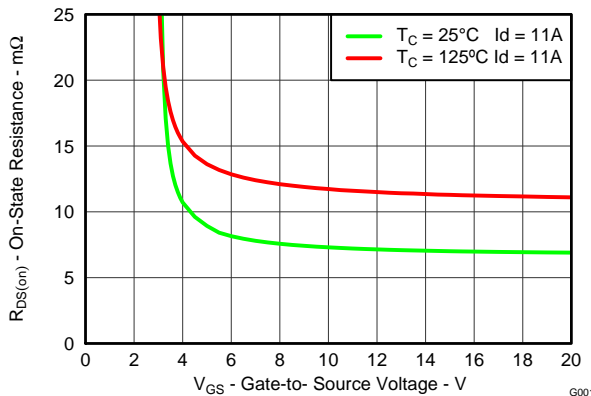
## 说明

NexFET™ 功率 MOSFET 被设计用于大大减少功率转换应用中的功率损失。

图 1. 顶视图



R<sub>DS</sub> (接通) 与 V<sub>GS</sub> 间的关系



## 产品概述

V <sub>DS</sub>	漏源电压	30	V
Q <sub>g</sub>	栅极电荷总量 (4.5V)	6.0	nC
Q <sub>gd</sub>	栅漏栅极电荷	1.4	nC
R <sub>DS</sub> (接通)	漏源导通电阻	V <sub>GS</sub> =4.5V	9 mΩ
		V <sub>GS</sub> =10V	7 mΩ
V <sub>GS(th)</sub>	阈值电压	1.7	V

## 订购信息

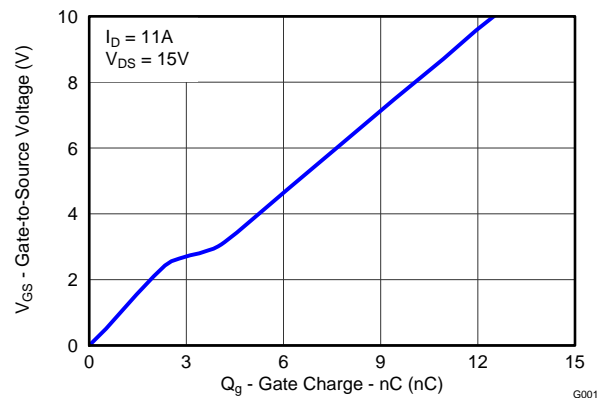
器件	封装	介质	数量	出货
CSD17551Q5A	5mm x 6mm SON 塑料封装	13 英寸卷带	2500	卷带封装

## 绝对最大额定值

T <sub>A</sub> =25°C 时测得, 除非另外说明		值	单位
V <sub>DS</sub>	漏源电压	30	V
V <sub>GS</sub>	栅源电压	±20	V
I <sub>D</sub>	持续漏极电流, T <sub>C</sub> =25°C 时	48	A
	持续漏极电流, T <sub>A</sub> =25°C 时 <sup>(1)</sup>	13.5	A
I <sub>DM</sub>	脉冲漏极电流, T <sub>A</sub> =25°C 时 <sup>(2)</sup>	85	A
P <sub>D</sub>	功率耗散 <sup>(1)</sup>	3	W
T <sub>J</sub> , T <sub>STG</sub>	运行结温和储存温度范围	-55 至 150	°C
E <sub>AS</sub>	雪崩能量, 单一脉冲 I <sub>D</sub> =25A, L=0.1mH, R <sub>G</sub> =25Ω 时	31.3	mJ

- (1) R<sub>θJA</sub>=41.9°C/W, 这是在一个厚度为 0.06 英寸 (1.52mm) 的 FR4 印刷电路板 (PCB) 上的 1 英寸<sup>2</sup> (6.45cm<sup>2</sup>), 2 盎司 (厚度为 0.071mm) 铜过渡垫片上测得的典型值。
- (2) 脉冲持续时间 ≤ 300μs, 占空比 ≤ 2%

## 栅极电荷



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

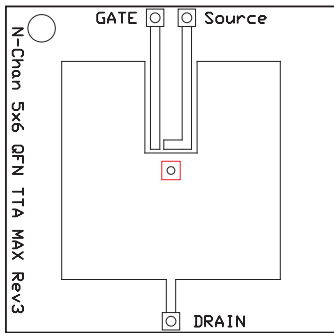
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Static Characteristics</b>						
B <sub>V</sub> DSS	Drain to Source Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 20V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.2	1.7	2.2	V
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11A		9	11	mΩ
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A		7	8.8	mΩ
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 11A		107		S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 15V, f = 1MHz		1060	1272	pF
C <sub>oss</sub>	Output Capacitance			247	296	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			19	24	pF
R <sub>G</sub>	Series Gate Resistance			1.4	1.9	Ω
Q <sub>g</sub>	Gate Charge Total (4.5V)	V <sub>DS</sub> = 15V, I <sub>D</sub> = 11A		6	7.2	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain			1.4		nC
Q <sub>gs</sub>	Gate Charge Gate to Source			2.8		nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>			1.6		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 13V, V <sub>GS</sub> = 0V		7.2		nC
t <sub>d(on)</sub>	Turn On Delay Time	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11A, R <sub>G</sub> = 2Ω		9.1		ns
t <sub>r</sub>	Rise Time			15.5		ns
t <sub>d(off)</sub>	Turn Off Delay Time			11.9		ns
t <sub>f</sub>	Fall Time			4.3		ns
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 11A, V <sub>GS</sub> = 0V		0.8	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DS</sub> = 13.5V, I <sub>F</sub> = 11A, di/dt = 300A/μs		8.7		nC
t <sub>rr</sub>	Reverse Recovery Time			13.5		ns

## THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

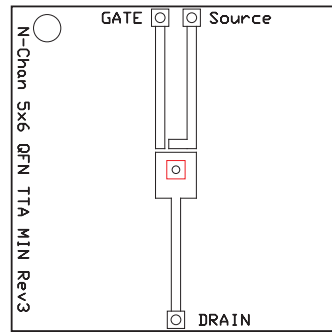
PARAMETER		MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Thermal Resistance Junction to Case <sup>(1)</sup>			4.2	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient <sup>(1)(2)</sup>			52.3	°C/W

- (1) R<sub>θJC</sub> is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



M0137-01

Max  $R_{\theta JA} = 52.3^{\circ}\text{C/W}$   
when mounted on  
1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-  
oz. (0.071-mm thick)  
Cu.



M0137-02

Max  $R_{\theta JA} = 133^{\circ}\text{C/W}$   
when mounted on a  
minimum pad area of  
2-oz. (0.071-mm thick)  
Cu.

### TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)

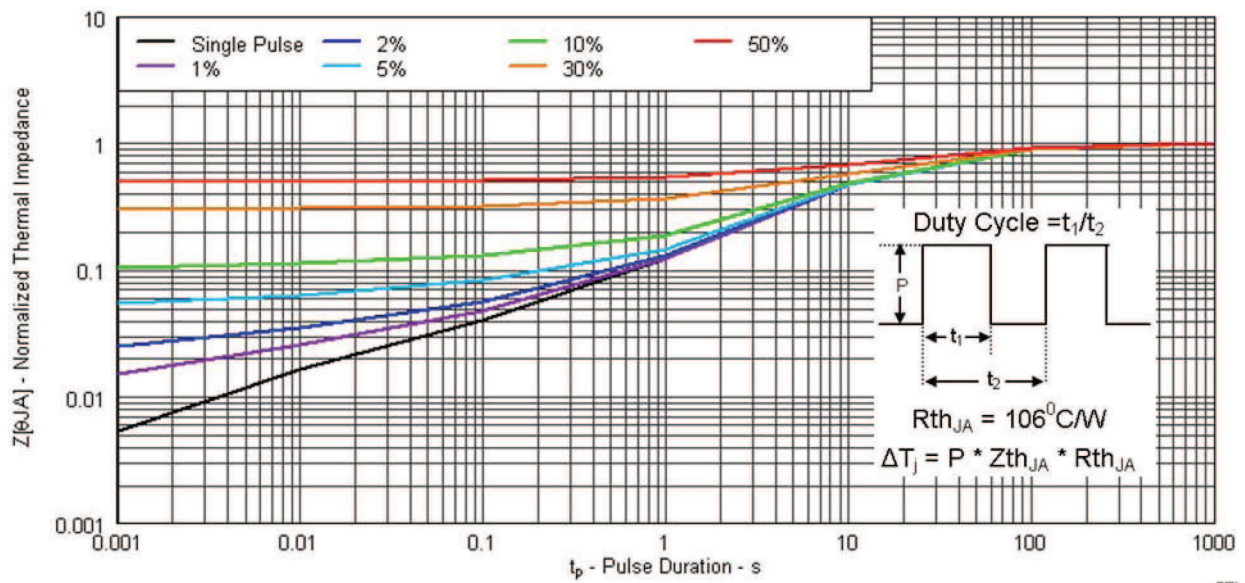
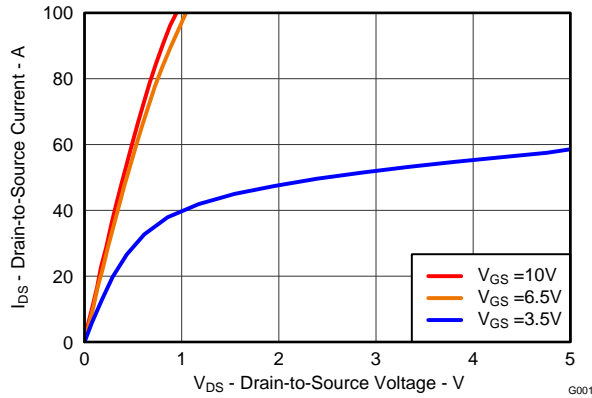


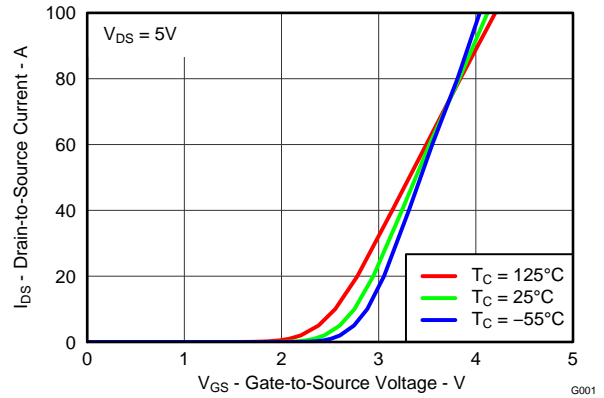
Figure 2. Transient Thermal Impedance

**TYPICAL MOSFET CHARACTERISTICS (continued)**

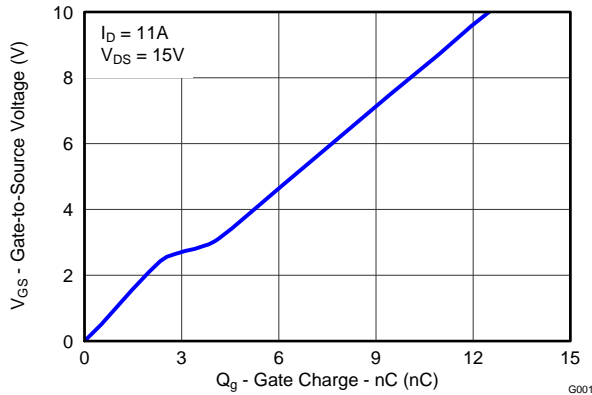
( $T_A = 25^\circ\text{C}$  unless otherwise stated)



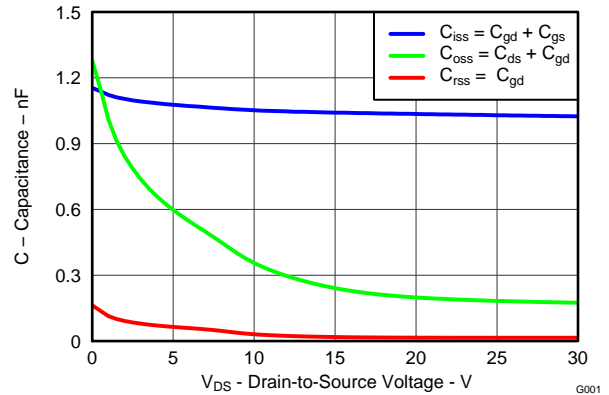
**Figure 3. Saturation Characteristics**



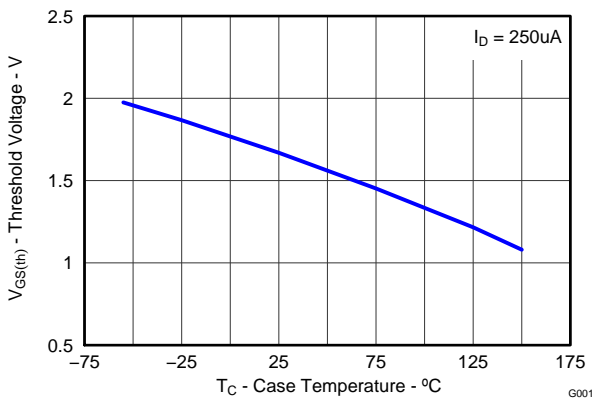
**Figure 4. Transfer Characteristics**



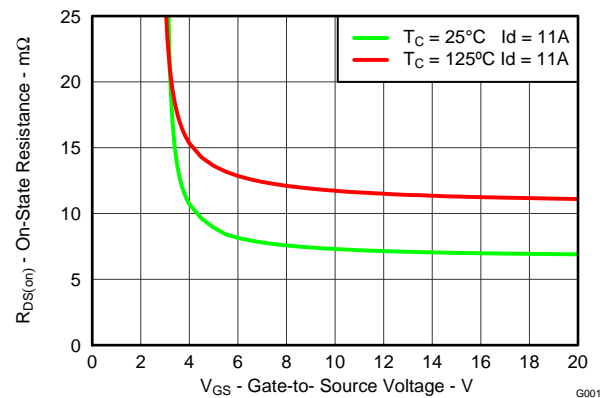
**Figure 5. Gate Charge**



**Figure 6. Capacitance**



**Figure 7. Threshold Voltage vs. Temperature**



**Figure 8. On-State Resistance vs. Gate-to-Source Voltage**

TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

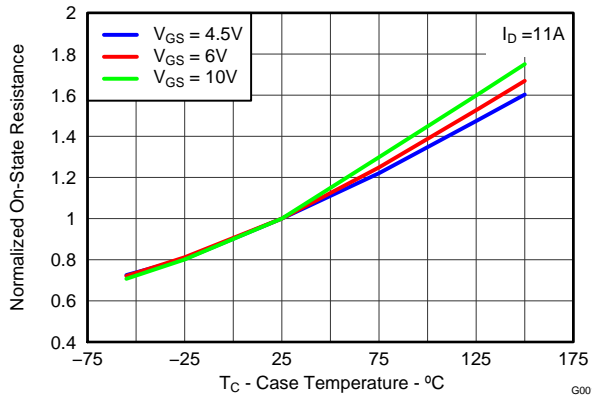


Figure 9. Normalized On-State Resistance vs. Temperature

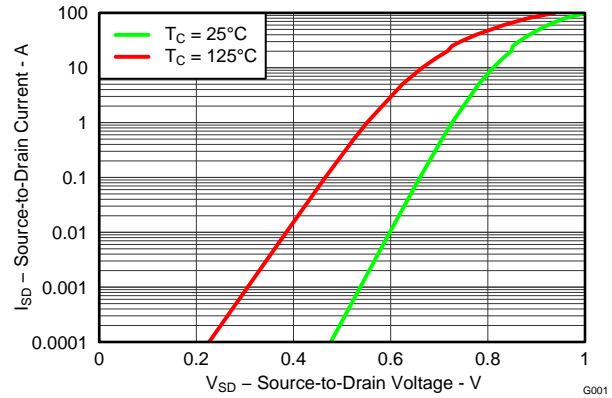


Figure 10. Typical Diode Forward Voltage

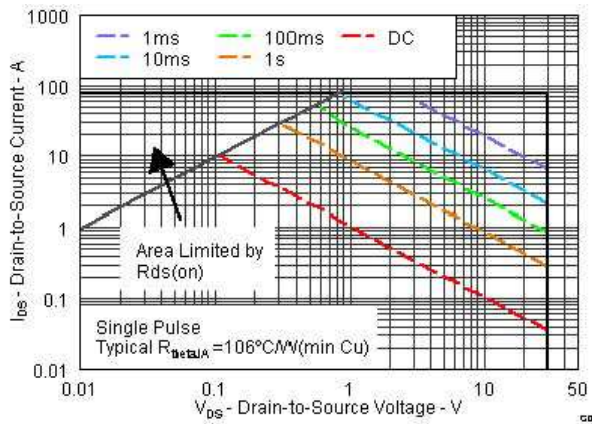


Figure 11. Maximum Safe Operating Area

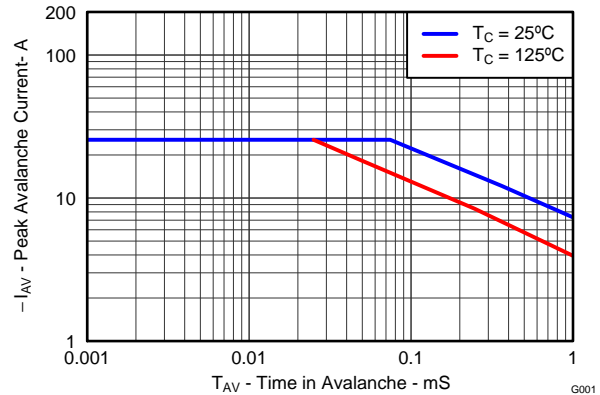


Figure 12. Single Pulse Unclamped Inductive Switching

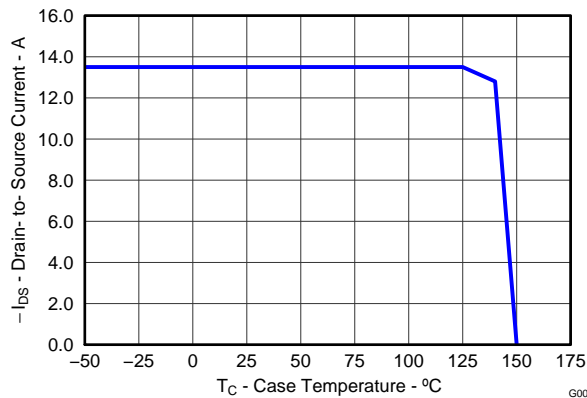


Figure 13. Maximum Drain Current vs. Temperature

**MECHANICAL DATA**

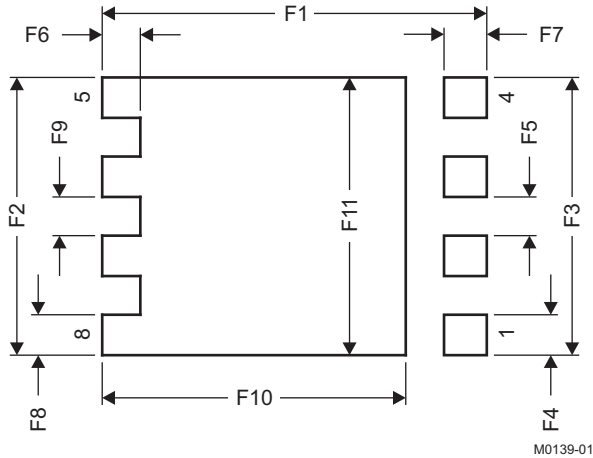
**Q5A Package Dimensions**



M0135-01

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.17	1.27	1.37
H	0.41	0.56	0.71
K	1.10		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
$\theta$	0°		12°

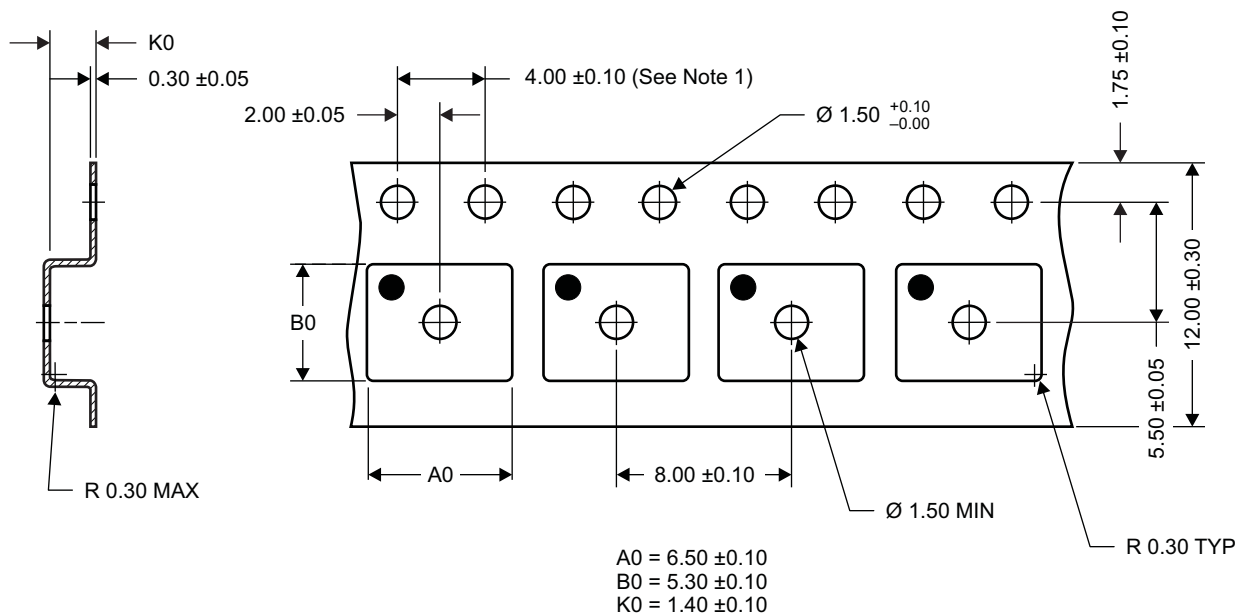
Figure 14. Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

### Q5A Tape and Reel Information



M0138-01

### Notes:

- 10-sprocket hole-pitch cumulative tolerance  $\pm 0.2$
- Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- Material: black static-dissipative polystyrene
- All dimensions are in mm (unless otherwise specified)
- A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">CSD17551Q5A</a>	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17551
CSD17551Q5A.B	Active	Production	VSONP (DQJ)   8	2500   LARGE T&R	ROHS Exempt	SN	Level-1-260C-UNLIM	-55 to 150	CSD17551

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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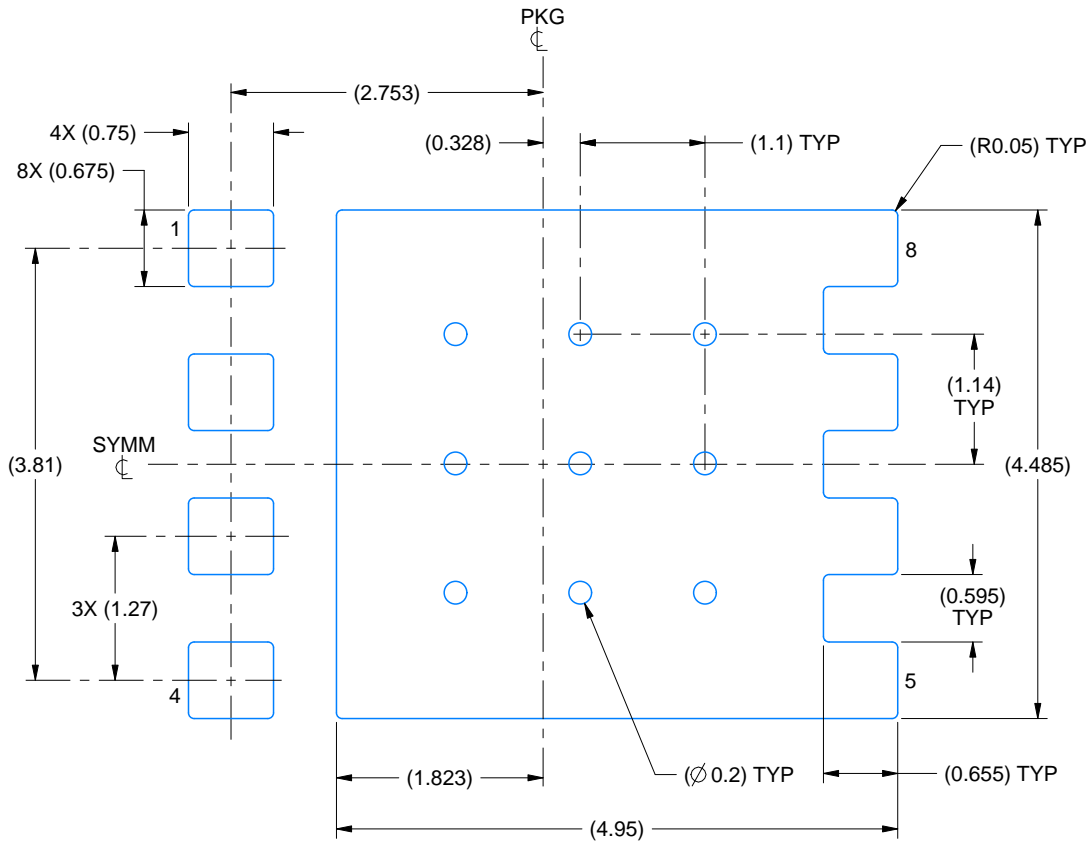


# EXAMPLE BOARD LAYOUT

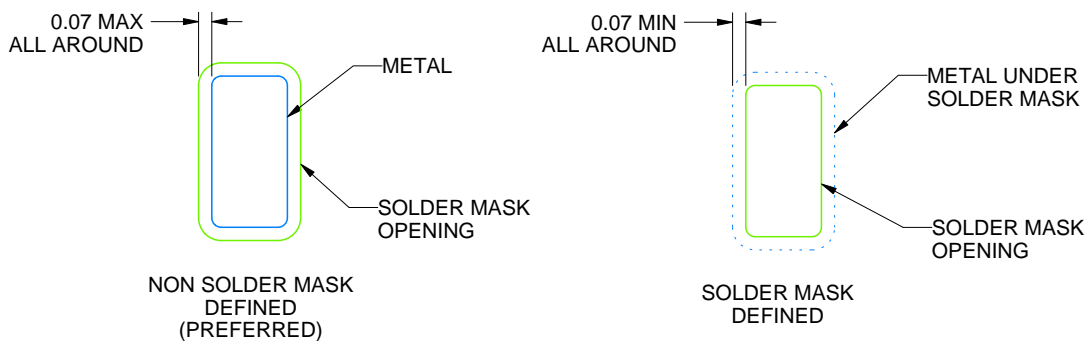
DQJ0008A

VSONP - 1.1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
SOLDER MASK DEFINED  
SCALE: 15X



SOLDER MASK DETAILS

4218866/C 02/2025

NOTES: (continued)

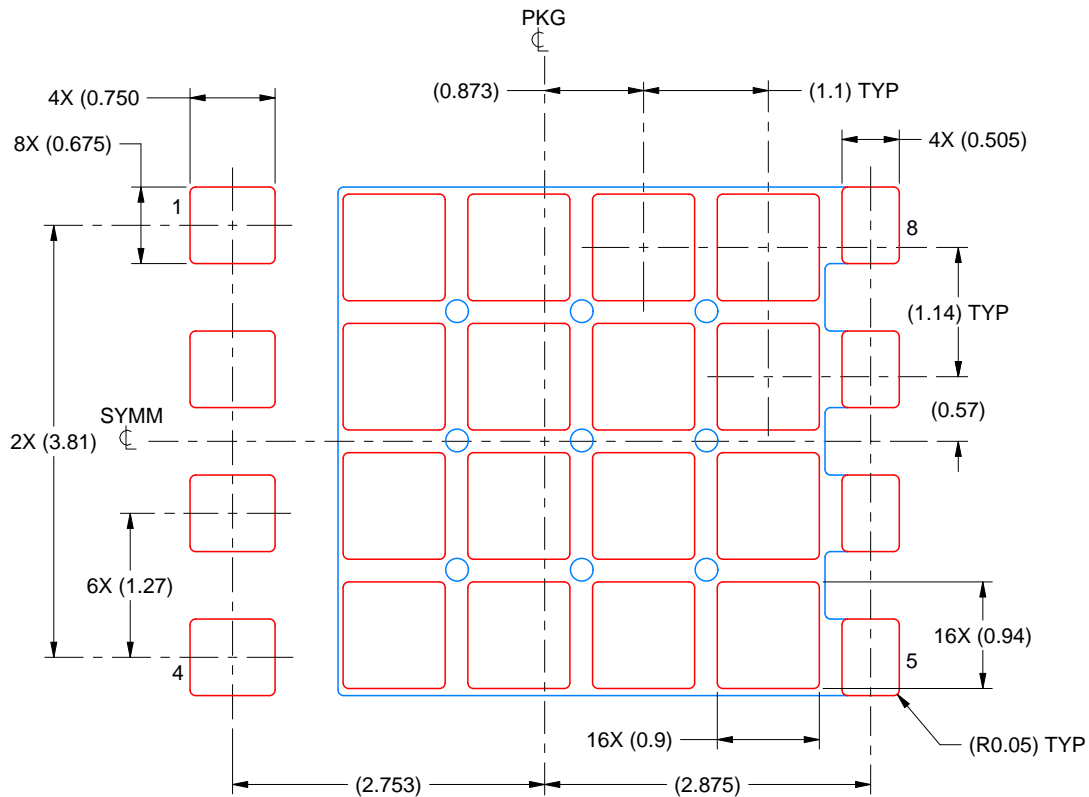
7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
8. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

# EXAMPLE STENCIL DESIGN

DQJ0008A

VSONP - 1.1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD:  
70% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE: 15X

4218866/C 02/2025

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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